

PBSS8110X

100 V, 1 A NPN low V_{CEsat} (BISS) transistor

Rev. 01 — 11 May 2005

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough in Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) SMD plastic package.

PNP complement: PBSS9110X.

1.2 Features

- SOT89 package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High efficiency leading to less heat generation

1.3 Applications

- Major application segments:
 - ◆ Automotive 42 V power
 - ◆ Telecom infrastructure
 - ◆ Industrial
- Peripheral driver:
 - ◆ Driver in low supply voltage applications (e.g. lamps and LEDs)
 - ◆ Inductive load driver (e.g. relays, buzzers and motors)
- DC-to-DC converter

1.4 Quick reference data

Table 1: Quick reference data

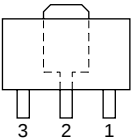
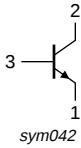
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	100	V
I_C	collector current (DC)		-	-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	3	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1$ A; $I_B = 100$ mA	[1]	-	165	200 mΩ

[1] Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	emitter		 sym042
2	collector		
3	base		

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PBSS8110X	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89

4. Marking

Table 4: Marking codes

Type number	Marking code [1]
PBSS8110X	*4B

[1] * = -: made in Hong Kong
* = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China

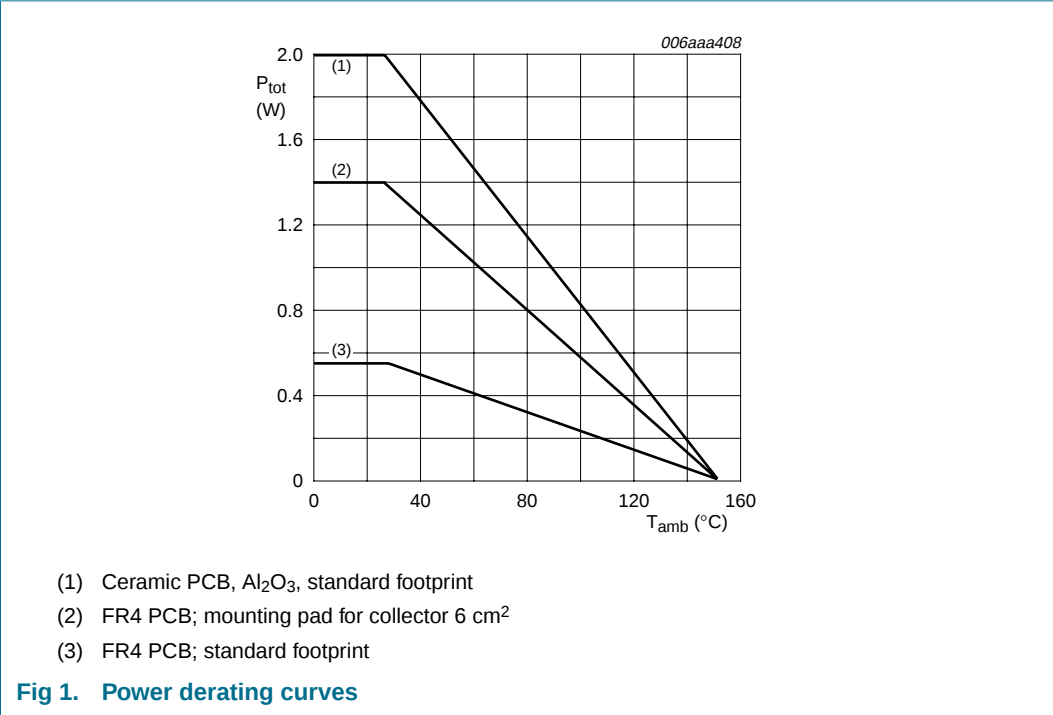


5. Limiting values

Table 5: Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	120	V
V_{CEO}	collector-emitter voltage	open base	-	100	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current (DC)		-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	3	A
I_B	base current (DC)		-	300	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1] -	0.55	W
			[2] -	1.4	W
			[3] -	2.0	W
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



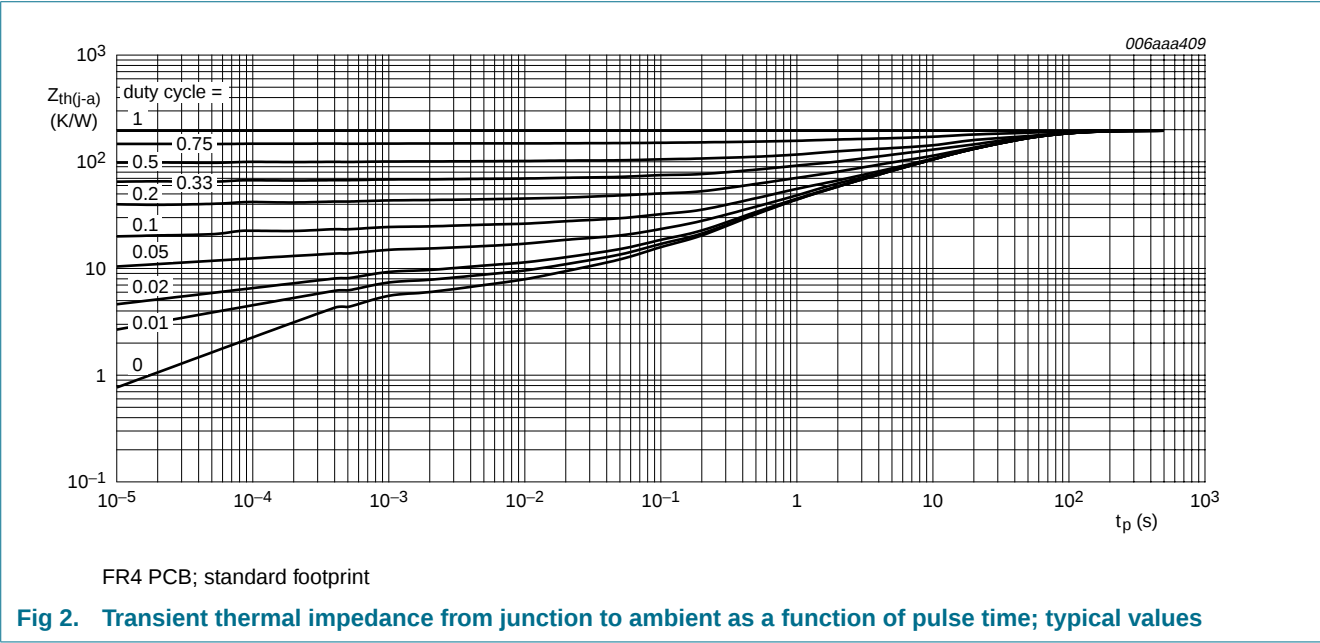


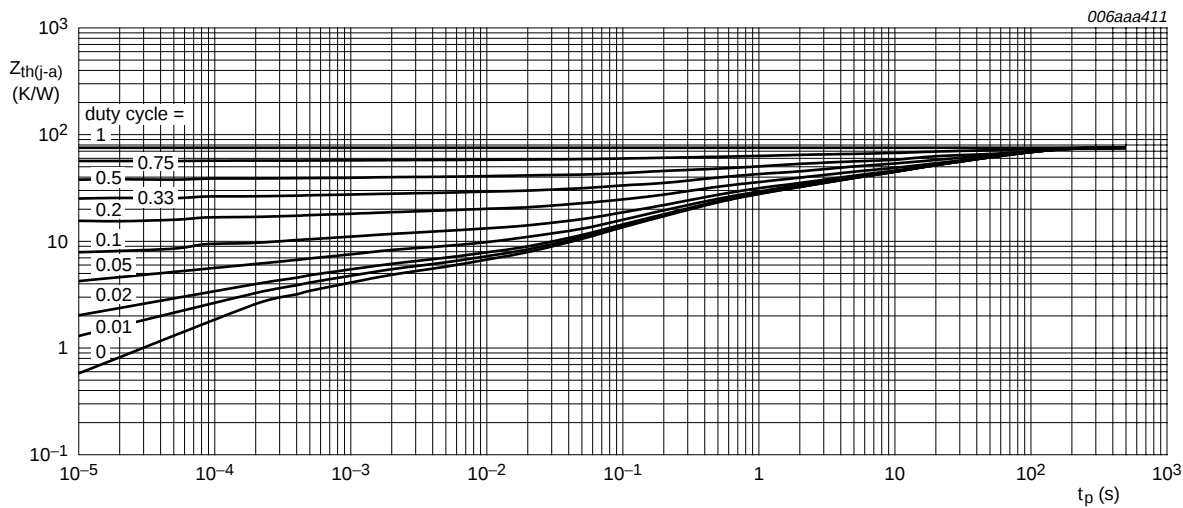
6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	227	K/W
			[2] -	-	89	K/W
			[3] -	-	63	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	16	K/W

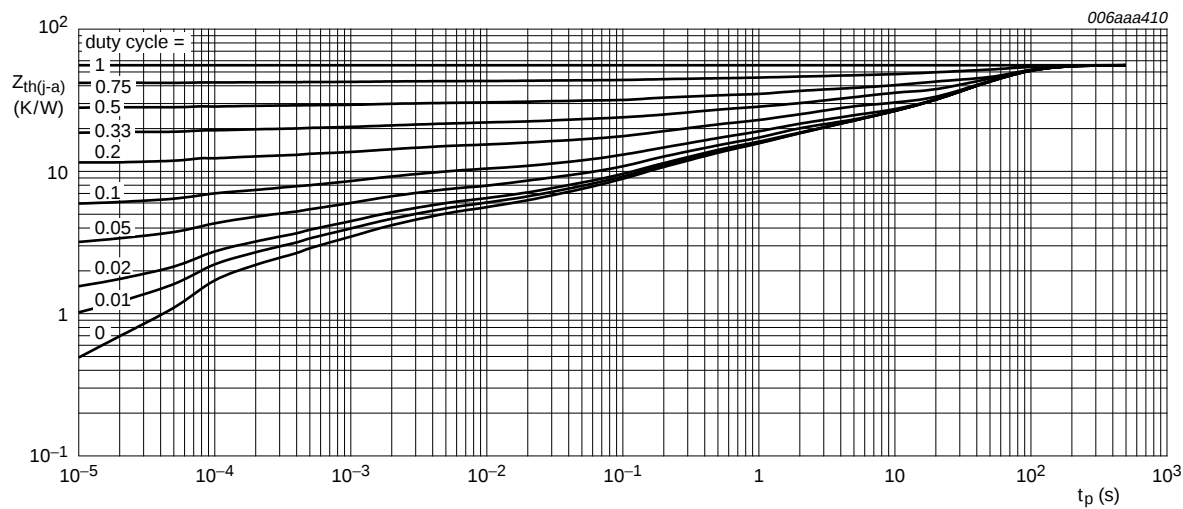
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.





FR4 PCB; mounting pad for collector 6 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



Ceramic PCB, Al₂O₃, standard footprint

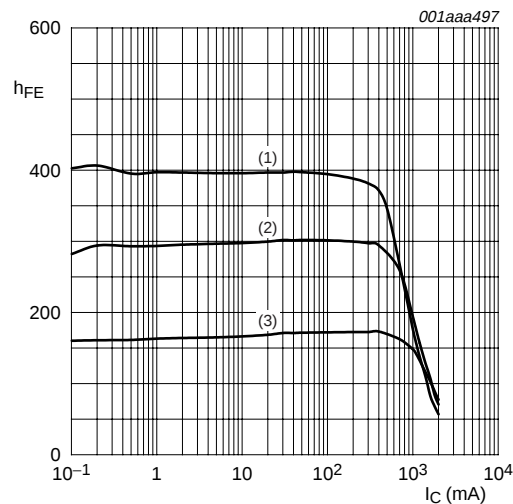
Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

7. Characteristics

Table 7: Characteristics
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

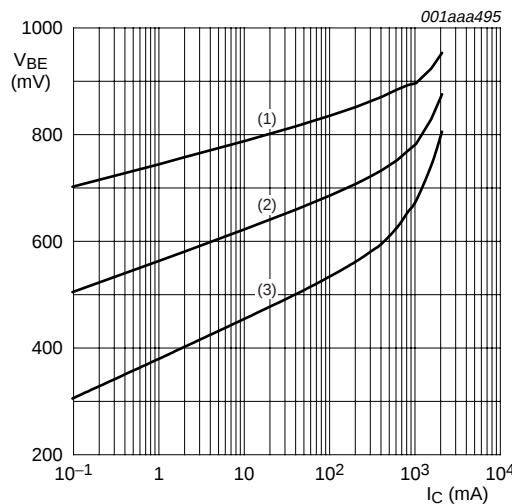
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 80\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
		$V_{CB} = 80\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = 80\text{ V}; V_{BE} = 0\text{ V}$	-	-	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 4\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}; I_C = 1\text{ mA}$	150	-	-	
		$V_{CE} = 10\text{ V}; I_C = 250\text{ mA}$	150	-	500	
		$V_{CE} = 10\text{ V}; I_C = 500\text{ mA}$	[1] 100	-	-	
		$V_{CE} = 10\text{ V}; I_C = 1\text{ A}$	[1] 80	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 10\text{ mA}$	-	-	40	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	-	-	120	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1] -	-	200	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1] -	165	200	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	-	-	1.05	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 10\text{ V}; I_C = 1\text{ A}$	-	-	0.9	V
t_d	delay time	$V_{CC} = 10\text{ V}; I_C = 0.5\text{ A}; I_{Bon} = 0.025\text{ A}; I_{Boff} = -0.025\text{ A}$	-	25	-	ns
t_r	rise time		-	220	-	ns
t_{on}	turn-on time		-	245	-	ns
t_s	storage time		-	365	-	ns
t_f	fall time		-	185	-	ns
t_{off}	turn-off time		-	550	-	ns
f_T	transition frequency	$V_{CE} = 10\text{ V}; I_C = 50\text{ mA}; f = 100\text{ MHz}$	100	-	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	7.5	pF

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.



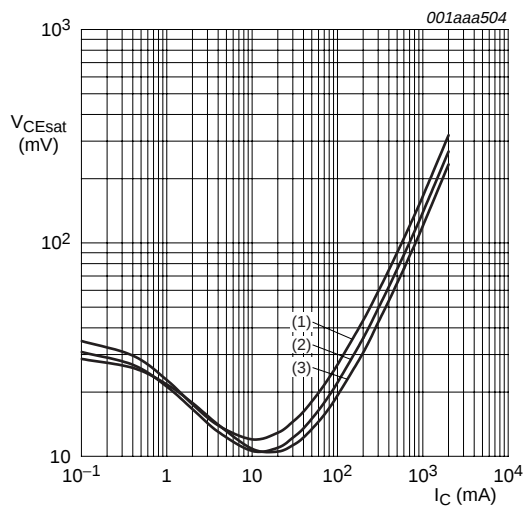
$V_{CE} = 10\text{ V}$
(1) $T_{amb} = 100\text{ °C}$
(2) $T_{amb} = 25\text{ °C}$
(3) $T_{amb} = -55\text{ °C}$

Fig 5. DC current gain as a function of collector current; typical values



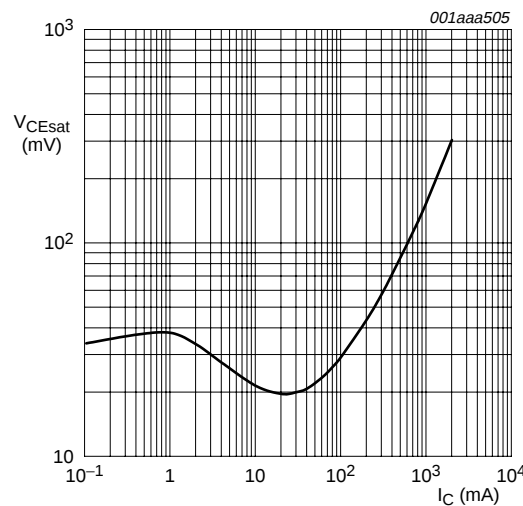
$V_{CE} = 10\text{ V}$
(1) $T_{amb} = -55\text{ °C}$
(2) $T_{amb} = 25\text{ °C}$
(3) $T_{amb} = 100\text{ °C}$

Fig 6. Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 10$
(1) $T_{amb} = 100\text{ °C}$
(2) $T_{amb} = 25\text{ °C}$
(3) $T_{amb} = -55\text{ °C}$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$; $T_{amb} = 25\text{ °C}$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

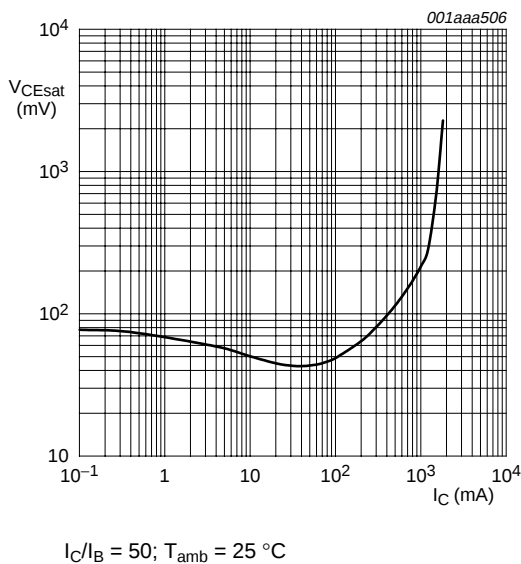


Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values

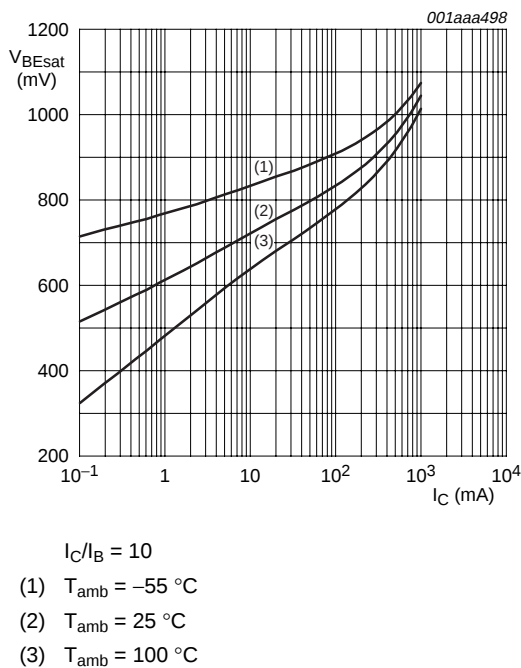


Fig 10. Base-emitter saturation voltage as a function of collector current; typical values

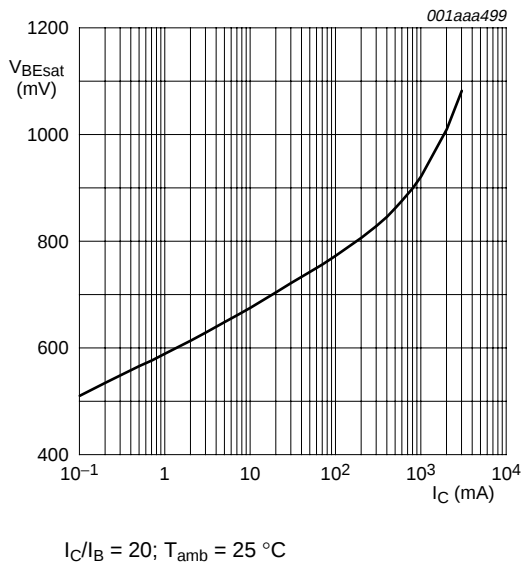


Fig 11. Base-emitter saturation voltage as a function of collector current; typical values

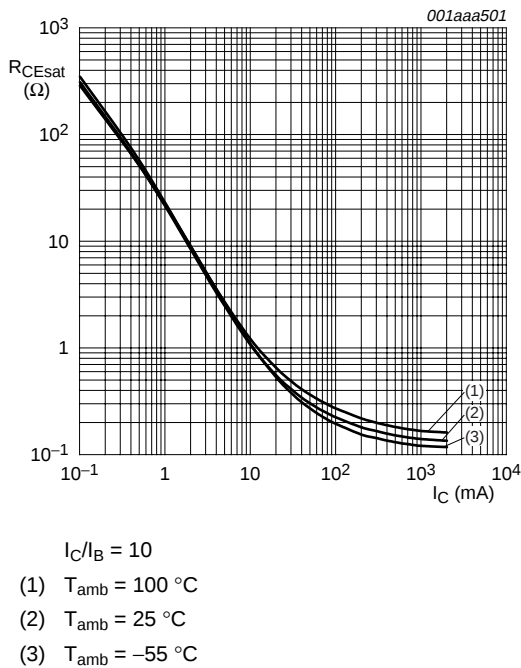
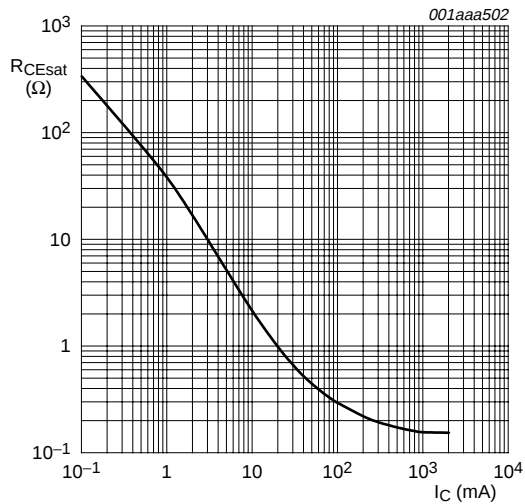
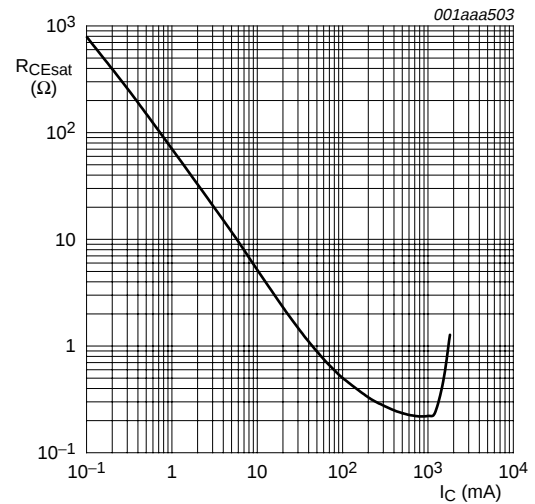


Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values



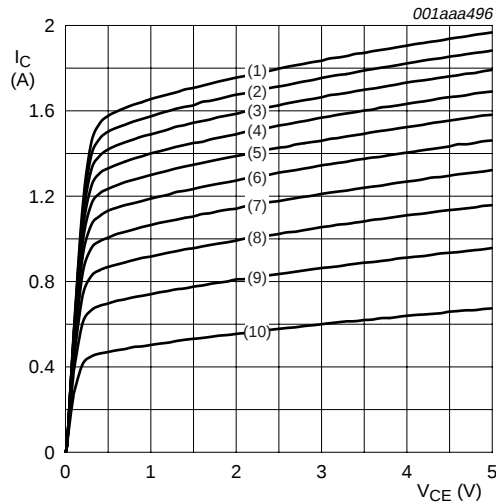
$I_C/I_B = 20$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 13. Collector-emitter saturation resistance as a function of collector current; typical values



$I_C/I_B = 50$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 14. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ }^{\circ}\text{C}$

- (1) $I_B = 35\text{ mA}$
- (2) $I_B = 31.5\text{ mA}$
- (3) $I_B = 28\text{ mA}$
- (4) $I_B = 24.5\text{ mA}$
- (5) $I_B = 21\text{ mA}$
- (6) $I_B = 17.5\text{ mA}$
- (7) $I_B = 14\text{ mA}$
- (8) $I_B = 10.5\text{ mA}$
- (9) $I_B = 7\text{ mA}$
- (10) $I_B = 3.5\text{ mA}$

Fig 15. Collector current as a function of collector-emitter voltage; typical values



8. Test information

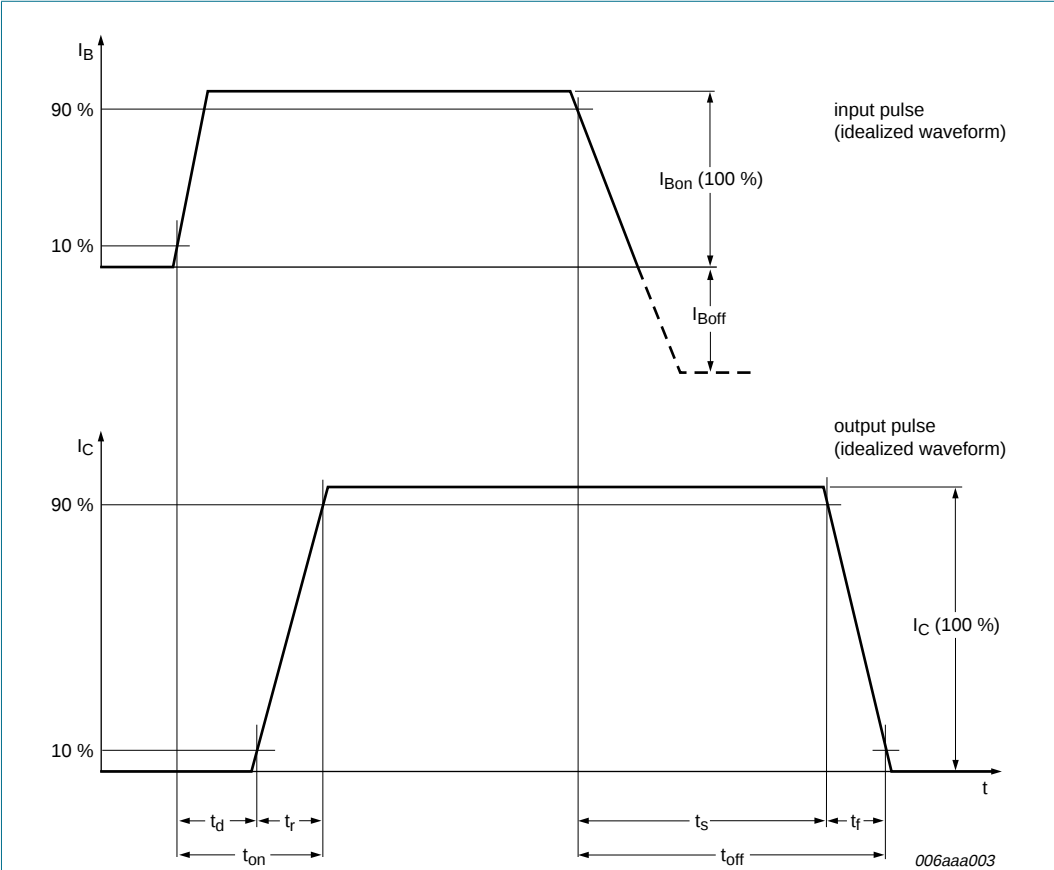


Fig 16. BISS transistor switching time definition

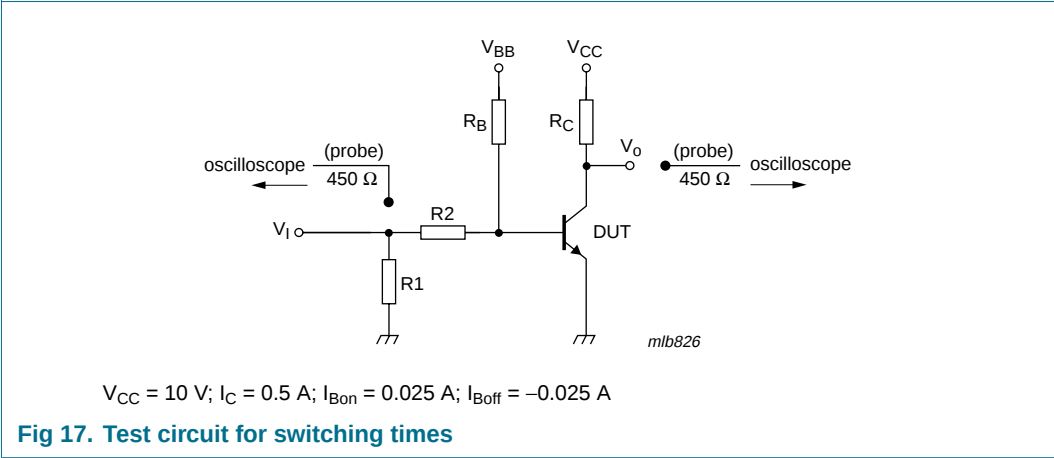
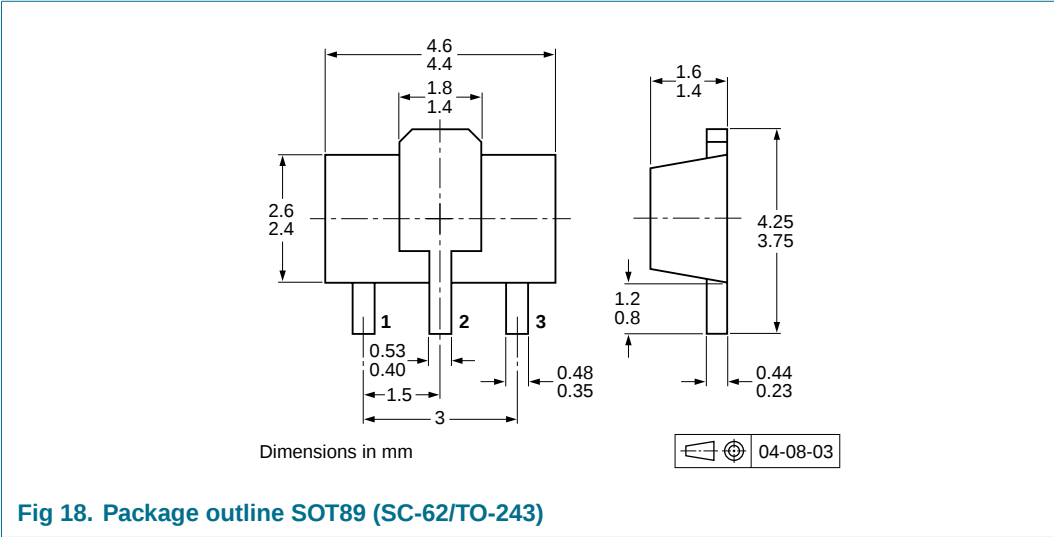


Fig 17. Test circuit for switching times



9. Package outline



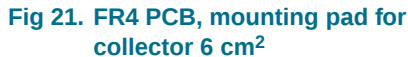
10. Packing information

Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [\[1\]](#)

Type number	Package	Description	Packing quantity	
			1000	4000
PBSS8110X	SOT89	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 18](#).





13. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PBSS8110X_1	20050511	Product data sheet	-	9397 750 14956	-

14. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

15. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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